
Fundamental Electrical Properties

1.1 Introduction

The atomic theory of matter specifies that each of the many chemical elements is composed of unique and identifiable particles called atoms. In ancient times only 10 were known in their pure, uncombined form; these were carbon, sulfur, copper, antimony, iron, tin, gold, silver, mercury, and lead. Of the several hundred now identified, less than 50 are found in an uncombined, or chemically free, form on earth.

Each atom consists of a compact nucleus of positively and negatively charged particles (protons and electrons, respectively). Additional electrons travel in well-defined orbits around the nucleus. The electron orbits are grouped in regions called *shells*, and the number of electrons in each orbit increases with the increase in orbit diameter in accordance with quantum-theory laws of physics. The diameter of the outer orbiting path of electrons in an atom is in the order of one-millionth (10^{-6}) millimeter, and the nucleus, one-millionth of that. These typical figures emphasize the minute size of the atom.

1.2 Electrical Fundamentals

The nucleus and the free electrons for an iron atom are shown in the schematic diagram in [Figure 1.1](#). Note that the electrons are spinning in different directions. This rotation creates a magnetic field surrounding each electron. If the number of electrons with positive spins is equal to the number with negative spins, then the net field is zero and the atom exhibits no magnetic field.

In the diagram, although the electrons in the first, second, and fourth shells balance each other, in the third shell five electrons have clockwise positive spins, and one counterclockwise negative spin, which gives the iron atom in this particular electron configuration a cumulative *magnetic effect*.

The parallel alignment of the electron spins over regions, known as *domains*, containing a large number of atoms. When a magnetic material is in a demagnetized state, the direction of magnetization in the domain is in a random order. Magnetization by an

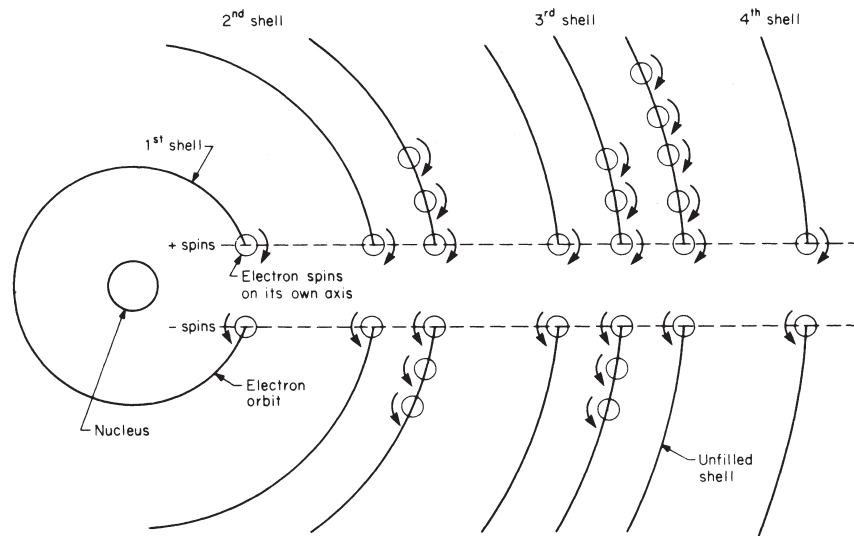


Figure 1.1 Schematic of the iron (Fe) atom.

external field takes place by a change or displacement in the isolation of the domains, with the result that a large number of the atoms are aligned with their charged electrons in parallel.

1.2.1 Conductors and Insulators

In some elements, such as copper, the electrons in the outer shells of the atom are so weakly bound to the nucleus that they can be released by a small electrical force, or voltage. A voltage applied between two points on a length of a metallic conductor produces the flow of an electric current, and an electric field is established around the conductor. The conductivity is a constant for each metal that is unaffected by the current through or the intensity of any external electric field.

In some nonmetallic materials, the free electrons are so tightly bound by forces in the atom that, upon the application of an external voltage, they will not separate from their atom except by an electrical force strong enough to destroy the insulating properties of the material. However, the charges will realign within the structure of their atom. This condition occurs in the insulating material (dielectric) of a capacitor when a voltage is applied to the two conductors encasing the dielectric.

Semiconductors are electronic conducting materials wherein the conductivity is dependent primarily upon impurities in the material. In addition to negative mobile charges of electrons, positive mobile charges are present. These positive charges are called *holes* because each exists as an absence of electrons. Holes (+) and electrons (-),

because they are oppositely charged, move in opposite directions in an electric field. The conductivity of semiconductors is highly sensitive to, and increases with, temperature.

1.2.2 Direct Current (dc)

Direct current is defined as a unidirectional current in which there are no significant changes in the current flow. In practice, the term frequently is used to identify a voltage source, in which case variations in the load can result in fluctuations in the current but not in the direction.

Direct current was used in the first systems to distribute electricity for household and industrial power. For safety reasons, and the voltage requirements of lamps and motors, distribution was at the low nominal voltage of 110. The losses in distribution circuits at this voltage seriously restricted the length of transmission lines and the size of the areas that could be covered. Consequently, only a relatively small area could be served by a single generating plant. It was not until the development of alternating-current systems and the voltage transformer that it was feasible to transport high levels of power at relatively low current over long distances for subsequent low-voltage distribution to consumers.

1.2.3 Alternating Current (ac)

Alternating current is defined as a current that reverses direction at a periodic rate. The average value of alternating current over a period of one cycle is equal to zero. The effective value of an alternating current in the supply of energy is measured in terms of the root mean square (rms) value. The rms is the square root of the square of all the values, positive and negative, during a complete cycle, usually a sine wave. Because rms values cannot be added directly, it is necessary to perform an rms addition as shown in the equation:

$$V_{rms\ total} = \sqrt{V_{rms\ 1}^2 + V_{rms\ 2}^2 + \dots + V_{rms\ n}^2} \quad (1.1)$$

As in the definition of direct current, in practice the term frequently is used to identify a voltage source.

The level of a sine-wave alternating current or voltage can be specified by two other methods of measurement in addition to rms. These are *average* and *peak*. A sine-wave signal and the rms and average levels are shown in [Figure 1.2](#). The levels of complex, symmetrical ac signals are specified as the peak level from the axis, as shown in the figure.

1.2.4 Static Electricity

The phenomenon of static electricity and related potential differences concerns configurations of conductors and insulators where no current flows and all electrical

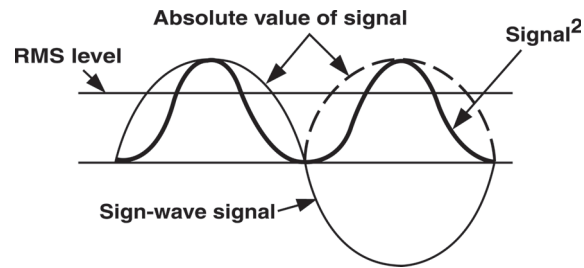


Figure 1.2 Root mean square (rms) measurements. The relationship of rms and average values is shown.

forces are unchanging; hence the term *static*. Nevertheless, static forces are present because of the number of excess electrons or protons in an object. A static charge can be induced by the application of a voltage to an object. A flow of current to or from the object can result from either a breakdown of the surrounding nonconducting material or by the connection of a conductor to the object.

Two basic laws regarding electrons and protons are:

- Like charges exert a repelling force on each other; electrons repel other electrons and protons repel other protons
- Opposite charges attract each other; electrons and protons are attracted to each other

Therefore, if two objects each contain exactly as many electrons as protons in each atom, there is no electrostatic force between the two. On the other hand, if one object is charged with an excess of protons (deficiency of electrons) and the other an excess of electrons, there will be a relatively weak attraction that diminishes rapidly with distance. An attraction also will occur between a neutral and a charged object.

Another fundamental law, developed by Faraday, governing static electricity is that all of the charge of any conductor not carrying a current lies in the surface of the conductor. Thus, any electric fields external to a completely enclosed metal box will not penetrate beyond the surface. Conversely, fields within the box will not exert any force on objects outside the box. The box need not be a solid surface; a conduction cage or grid will suffice. This type of isolation frequently is referred to as a *Faraday shield*.

1.2.5 Noise in Electronic Circuits

Noise has become the standard term for signals that are random and that are combined with the circuit signal to affect the overall performance of a system. As the study of noise has progressed, engineers have come to realize that there are many sources of noise in circuits. The following definitions are commonly used in discussions of circuit noise:

- *White noise*: a signal that has its energy evenly distributed over the entire frequency spectrum, within the frequency range of interest (typically below frequencies in the infrared range). Because *white noise* is totally random, it may seem inappropriate to refer to its frequency range, because it is not really periodic in the ordinary sense. Nevertheless, by examining an oscilloscope trace of white noise, it can be verified that every trace is different, as the noise never repeats itself, and yet each trace looks the same. There is a strong theoretical foundation to represent the frequency content of such signals as covering the frequency spectrum evenly. In this way the impact on other periodic signals can be analyzed. The term white noise arises from the fact that, similar to white light, which has equal amounts of all light frequencies, white noise has equal amounts of noise at all frequencies within circuit operating ranges.
- *Interference*: the name given to any predictable, periodic signal that occurs in an electronic circuit in addition to the signal the circuit is designed to process. This is distinguished from a noise signal by the fact that it occupies a relatively small frequency range, and because it is predictable it can often be filtered out. Usually, interference comes from another electronic system such as an interfering radio source.
- *Thermal noise*: any noise that is generated within a circuit and is temperature-dependent. This signal usually is the result of the influence of temperature directly on the operating characteristics of circuit components, which because of the random motion of molecules as a result of temperature, in turn creates a random fluctuation of the signal being processed.
- *Shot noise*: a type of circuit noise that is not temperature-dependent, and is not white noise in the sense that it tends to diminish at higher frequencies. This noise usually occurs in components whose operation depends on a mean *particle residence time* for the active electrons within the device. The *cutoff frequency* above which noise disappears is closely related to the inverse of this characteristic particle residence time.

1.3 References

1. Whitaker, Jerry C. (ed.), *The Electronics Handbook*, CRC Press, Boca Raton, FL, 1996.

1.4 Bibliography

- Benson, K. Blair, and Jerry C. Whitaker, *Television and Audio Handbook for Technicians and Engineers*, McGraw-Hill, New York, NY, 1990.
- Benson, K. Blair, *Audio Engineering Handbook*, McGraw-Hill, New York, NY, 1988.
- Whitaker, Jerry C., *Television Engineers' Field Manual*, McGraw-Hill, New York, NY, 2000.

1.5 Tabular Data

Table 1.1 Symbols and Terminology for Physical and Chemical Quantities: Classical Mechanics (From [1]. Used with permission.)

Name	Symbol	Definition	SI unit
mass	m		kg
reduced mass	μ	$\mu = m_1 m_2 / (m_1 + m_2)$	kg
density, mass density	ρ	$\rho = m/V$	kg m^{-3}
relative density	d	$d = \rho/\rho^0$	1
surface density	ρ_A, ρ_S	$\rho_A = m/A$	kg m^{-2}
specific volume	v	$v = V/M = 1/\rho$	$\text{m}^3 \text{kg}^{-1}$
momentum	\mathbf{p}	$\mathbf{p} = m\mathbf{v}$	kg ms^{-1}
angular momentum, action	L	$L = \mathbf{r} \times \mathbf{p}$	J s
moment of inertia	I, J	$I = \sum m_i r_i^2$	kg m^2
force	\mathbf{F}	$\mathbf{F} = d\mathbf{p}/dt = m\mathbf{a}$	N
torque, moment of a force	$\mathbf{T}, (\mathbf{M})$	$\mathbf{T} = \mathbf{r} \times \mathbf{F}$	N m
energy	E		J
potential energy	E_p, V, Φ	$E_p = -\int \mathbf{F} \cdot d\mathbf{s}$	J
kinetic energy	E_k, T, K	$E_k = (1/2)mv^2$	J
work	W, w	$W = \int \mathbf{F} \cdot d\mathbf{s}$	J
Hamilton function	H	$H(q, p)$ $= T(q, p) + V(q)$	J
Lagrange function	L	$L(q, \dot{q})$ $= T(q, \dot{q}) - V(q)$	J
pressure	p, P	$p = F/A$	$\text{Pa}, \text{N m}^{-2}$
surface tension	γ, σ	$\gamma = dW/dA$	$\text{N m}^{-1}, \text{J m}^{-2}$
weight	$G, (W, P)$	$G = mg$	N
gravitational constant	G	$F = Gm_1 m_2 / r^2$	$\text{N m}^2 \text{kg}^{-2}$
normal stress	σ	$\sigma = F/A$	Pa
shear stress	τ	$\tau = F/A$	Pa
linear strain, relative elongation	ε, e	$\varepsilon = \Delta l/l$	1
modulus of elasticity, Young's modulus	E	$E = \sigma/\varepsilon$	Pa
shear strain	γ	$\gamma = \Delta x/d$	1
shear modulus	G	$G = \tau/\gamma$	Pa
volume strain, bulk strain	θ	$\theta = \Delta V/V_0$	1
bulk modulus, compression modulus	K, μ	$K = -V_0(dp/dV)$ $\tau_{x,z} = \eta(dv_x/dz)$	Pa
viscosity, dynamic viscosity			
fluidity	ϕ	$\phi = 1/\eta$	$\text{m kg}^{-1} \text{s}$
kinematic viscosity	ν	$\nu = \eta/\rho$	$\text{m}^2 \text{s}^{-1}$
friction coefficient	$\mu, (f)$	$F_{\text{frict}} = \mu F_{\text{norm}}$	1
power	P	$P = dW/dt$	W
sound energy flux	P, P_a	$P = dE/dt$	W
acoustic factors			
reflection factor	ρ	$\rho = P_r/P_0$	1
acoustic absorption factor	$\alpha_a, (\alpha)$	$\alpha_a = 1 - \rho$	1
transmission factor	τ	$\tau = P_t/P_0$	1
dissipation factor	δ	$\delta = \alpha_a - \tau$	1

Table 1.2 Symbols and Terminology for Physical and Chemical Quantities: Electricity and Magnetism (From [1]. Used with permission.)

Name	Symbol	Definition	SI unit
quantity of electricity, electric charge	Q		C
charge density	ρ	$\rho = Q/V$	C m^{-3}
surface charge density	σ	$\sigma = Q/A$	C m^{-2}
electric potential	V, ϕ	$V = dW/dQ$	V, J C^{-1}
electric potential difference	$U, \Delta V, \Delta\phi$	$U = V_2 - V_1$	V
electromotive force	E	$E = \int (\mathbf{F}/Q) \cdot d\mathbf{s}$	V
electric field strength	\mathbf{E}	$\mathbf{E} = \mathbf{F}/Q = -\text{grad } V$	V m^{-1}
electric flux	Ψ	$\Psi = \int \mathbf{D} \cdot d\mathbf{A}$	C
electric displacement	\mathbf{D}	$\mathbf{D} = \epsilon\mathbf{E}$	C m^{-2}
capacitance	C	$C = Q/U$	F, C V^{-1}
permittivity	ϵ	$\mathbf{D} = \epsilon\mathbf{E}$	F m^{-1}
permittivity of vacuum	ϵ_0	$\epsilon_0 = \mu_0^{-1} c_0^{-2}$	F m^{-1}
relative permittivity	ϵ_r	$\epsilon_r = \epsilon/\epsilon_0$	1
dielectric polarization (dipole moment per volume)	\mathbf{P}	$\mathbf{P} = \mathbf{D} - \epsilon_0\mathbf{E}$	C m^{-2}
electric susceptibility	χ_e	$\chi_e = \epsilon_r - 1$	1
electric dipole moment	\mathbf{p}, μ	$\mathbf{p} = Q\mathbf{r}$	C m
electric current	I	$I = dQ/dt$	A
electric current density	\mathbf{j}, \mathbf{J}	$I = \int \mathbf{j} \cdot d\mathbf{A}$	A m^{-2}
magnetic flux density, magnetic induction	\mathbf{B}	$\mathbf{F} = Q\mathbf{v} \times \mathbf{B}$	T
magnetic flux	Φ	$\Phi = \int \mathbf{B} \cdot d\mathbf{A}$	Wb
magnetic field strength	\mathbf{H}	$\mathbf{B} = \mu\mathbf{H}$	A m^{-1}
permeability	μ	$\mathbf{B} = \mu\mathbf{H}$	$\text{N A}^{-2}, \text{H m}^{-1}$
permeability of vacuum	μ_0		H m^{-1}
relative permeability	μ_r	$\mu_r = \mu/\mu_0$	1
magnetization (magnetic dipole moment per volume)	\mathbf{M}	$\mathbf{M} = \mathbf{B}/\mu_0 - \mathbf{H}$	A m^{-1}
magnetic susceptibility	$\chi, \kappa, (\chi_m)$	$\chi = \mu_r - 1$	1
molar magnetic susceptibility	χ_m	$\chi_m = V_m\chi$	$\text{m}^3 \text{mol}^{-1}$
magnetic dipole moment	\mathbf{m}, μ	$E_p = -\mathbf{m} \cdot \mathbf{B}$	$\text{A m}^2, \text{J T}^{-1}$
electrical resistance	R	$R = U/I$	Ω
conductance	G	$G = 1/R$	S
loss angle	δ	$\delta = (\pi/2) + \phi_I - \phi_U$	1, rad
reactance	X	$X = (U/I) \sin \delta$	Ω
impedance (complex impedance)	Z	$Z = R + iX$	Ω
admittance (complex admittance)	Y	$Y = 1/Z$	S
susceptance	B	$Y = G + iB$	S
resistivity	ρ	$\rho = E/j$	$\Omega \text{ m}$
conductivity	κ, γ, σ	$\kappa = 1/\rho$	S m^{-1}
self-inductance	L	$E = -L(dI/dt)$	H
mutual inductance	M, L_{12}	$E_1 = L_{12}(dI_2/dt)$	H
magnetic vector potential	\mathbf{A}	$\mathbf{B} = \nabla \times \mathbf{A}$	Wb m^{-1}
Poynting vector	\mathbf{S}	$\mathbf{S} = \mathbf{E} \times \mathbf{H}$	W m^{-2}

Table 1.3 Symbols and Terminology for Physical and Chemical Quantities: Electromagnetic Radiation (From [1]. Used with permission.)

Name	Symbol	Definition	SI unit
wavelength	λ		m
speed of light in vacuum	c_0		m s ⁻¹
in a medium	c	$c = c_0/n$	m s ⁻¹
wavenumber in vacuum	$\tilde{\nu}$	$\tilde{\nu} = \nu/c_0 = 1/n\lambda$	m ⁻¹
wavenumber (in a medium)	σ	$\sigma = 1/\lambda$	m ⁻¹
frequency	ν	$\nu = c/\lambda$	Hz
circular frequency, pulsatance	ω	$\omega = 2\pi\nu$	s ⁻¹ , rad s ⁻¹
refractive index	n	$n = c_0/c$	1
Planck constant	h		J s
Planck constant/2 π	\hbar	$\hbar = h/2\pi$	J s
radiant energy	Q, W		J
radiant energy density	ρ, w	$\rho = Q/V$	J m ⁻³
spectral radiant energy density			
in terms of frequency	ρ_ν, w_ν	$\rho_\nu = d\rho/d\nu$	J m ⁻³ Hz ⁻¹
in terms of wavenumber	$\rho_{\tilde{\nu}}, w_{\tilde{\nu}}$	$\rho_{\tilde{\nu}} = d\rho/d\tilde{\nu}$	J m ⁻²
in terms of wavelength	ρ_λ, w_λ	$\rho_\lambda = d\rho/d\lambda$	J m ⁻⁴
Einstein transition probabilities			
spontaneous emission	A_{nm}	$dN_n/dt = -A_{nm}N_n$	s ⁻¹
stimulated emission	B_{nm}	$dN_n/dt = -\rho_{\tilde{\nu}}(\tilde{\nu}_{nm}) \times B_{nm}N_n$	s kg ⁻¹
stimulated absorption	B_{mn}	$dN_n/dt = \rho_{\tilde{\nu}}(\tilde{\nu}_{nm})B_{mn}N_m$	s kg ⁻¹
radiant power, radiant energy per time	Φ, P	$\Phi = dQ/dt$	W
radiant intensity	I	$I = d\Phi/d\Omega$	W sr ⁻¹
radiant exitance (emitted radiant flux)	M	$M = d\Phi/dA_{\text{source}}$	W m ⁻²
irradiance (radiant flux received)	$E, (I)$	$E = d\Phi/dA$	W m ⁻²
emittance	ε	$\varepsilon = M/M_{\text{bb}}$	1
Stefan-Boltzman constant	σ	$M_{\text{bb}} = \sigma T^4$	W m ⁻² K ⁻⁴
first radiation constant	c_1	$c_1 = 2\pi hc_0^2$	W m ²
second radiation constant	c_2	$c_2 = hc_0/k$	K m
transmittance, transmission factor	τ, T	$\tau = \Phi_{\text{tr}}/\Phi_0$	1
absorptance, absorption factor	α	$\alpha = \Phi_{\text{abs}}/\Phi_0$	1
reflectance, reflection factor	ρ	$\rho = \Phi_{\text{refl}}/\Phi_0$	1
(decadic) absorbance	A	$A = \lg(1 - \alpha_i)$	1
napierian absorbance	B	$B = \ln(1 - \alpha_i)$	1
absorption coefficient			
(linear) decadic	a, K	$a = A/l$	m ⁻¹
(linear) napierian	α	$\alpha = B/l$	m ⁻¹
molar (decadic)	ε	$\varepsilon = a/c = A/cl$	m ² mol ⁻¹
molar napierian	κ	$\kappa = \alpha/c = B/cl$	m ² mol ⁻¹
absorption index	k	$k = \alpha/4\pi\tilde{\nu}$	1
complex refractive index	\hat{n}	$\hat{n} = n + ik$	1
molar refraction	R, R_m	$R = \frac{n^2 - 1}{n^2 + 2} V_m$	m ³ mol ⁻¹
angle of optical rotation	α		1, rad

Table 1.4 Symbols and Terminology for Physical and Chemical Quantities: Solid State
(From [1]. Used with permission.)

Name	Symbol	Definition	SI unit
lattice vector	\mathbf{R}, \mathbf{R}_0		m
fundamental translation vectors for the crystal lattice	$\mathbf{a}_1; \mathbf{a}_2; \mathbf{a}_3,$ $\mathbf{a}; \mathbf{b}; \mathbf{c}$	$\mathbf{R} = n_1 \mathbf{a}_1 + n_2 \mathbf{a}_2 + n_3 \mathbf{a}_3$	m
(circular) reciprocal lattice vector	\mathbf{G}	$\mathbf{G} \cdot \mathbf{R} = 2\pi m$	m^{-1}
(circular) fundamental translation vectors for the reciprocal lattice	$\mathbf{b}_1; \mathbf{b}_2; \mathbf{b}_3,$ $\mathbf{a}^*; \mathbf{b}^*; \mathbf{c}^*$	$\mathbf{a}_i \cdot \mathbf{b}_k = 2\pi \delta_{ik}$	m^{-1}
lattice plane spacing	d		m
Bragg angle	θ	$n\lambda = 2d \sin \theta$	1, rad
order of reflection	n		1
order parameters			
short range	σ		1
long range	s		1
Burgers vector	\mathbf{b}		m
particle position vector	\mathbf{r}, \mathbf{R}_j		m
equilibrium position	\mathbf{R}_0		m
vector of an ion			
equilibrium position	\mathbf{R}_0		m
vector of an ion			
displacement vector of an ion	\mathbf{u}	$\mathbf{u} = \mathbf{R} - \mathbf{R}_0$	m
Debye–Waller factor	B, D		1
Debye circular wavenumber	q_D		m^{-1}
Debye circular frequency	ω_D		s^{-1}
Grüneisen parameter	γ, Γ	$\gamma = \alpha V / \kappa C_V$	1
Madelung constant	α, \mathcal{M}	$E_{\text{coul}} = \frac{\alpha N_A z_+ z_- e^2}{4\pi \epsilon_0 R_0}$	1
density of states	N_E	$N_E = dN(E)/dE$	$\text{J}^{-1} \text{m}^{-3}$
(spectral) density of vibrational modes	N_ω, g	$N_\omega = dN(\omega)/d\omega$	s m^{-3}
resistivity tensor	ρ_{ik}	$E = \rho \cdot \mathbf{j}$	$\Omega \text{ m}$
conductivity tensor	σ_{ik}	$\sigma = \rho^{-1}$	S m^{-1}
thermal conductivity tensor	λ_{ik}	$\mathbf{J}_q = -\lambda \cdot \text{grad } T$	$\text{W m}^{-1} \text{K}^{-1}$
residual resistivity	ρ_R		$\Omega \text{ m}$
relaxation time	τ	$\tau = l/v_F$	s
Lorenz coefficient	L	$L = \lambda/\sigma T$	$\text{V}^2 \text{K}^{-2}$
Hall coefficient	A_H, R_H	$E = \rho \cdot \mathbf{j} + R_H(\mathbf{B} \times \mathbf{j})$	$\text{m}^3 \text{C}^{-1}$
thermoelectric force	E		V
Peltier coefficient	Π		V
Thomson coefficient	$\mu, (\tau)$		V K^{-1}
work function	Φ	$\Phi = E_\infty - E_F$	J
number density,	$n, (p)$		m^{-3}
number concentration			
gap energy	E_g		J
donor ionization energy	E_d		J
acceptor ionization energy	E_a		J
Fermi energy	E_F, ϵ_F		J
circular wave vector,	\mathbf{k}, \mathbf{q}	$k = 2\pi/\lambda$	m^{-1}
propagation vector			
Bloch function	$u_k(\mathbf{r})$	$\psi(\mathbf{r}) = u_k(\mathbf{r}) \exp(i\mathbf{k} \cdot \mathbf{r})$	$\text{m}^{-3/2}$
charge density of electrons	ρ	$\rho(\mathbf{r}) = -e\psi^*(\mathbf{r})\psi(\mathbf{r})$	C m^{-3}
effective mass	m^*		kg
mobility	μ	$\mu = v_{\text{drift}}/E$	$\text{m}^2 \text{V}^{-1} \text{s}^{-1}$
mobility ratio	b	$b = \mu_n/\mu_p$	1
diffusion coefficient	D	$dN/dt = -DA(dn/dx)$	$\text{m}^2 \text{s}^{-1}$
diffusion length	L	$L = \sqrt{D\tau}$	m
characteristic (Weiss) temperature	ϕ, ϕ_w		K
Curie temperature	T_C		K
Néel temperature	T_N		K

Table 1.5 Total Elongation at Failure of Selected Polymers (*From [1]. Used with permission.*)

Polymer	Elongation
ABS	5–20
Acrylic	2–7
Epoxy	4.4
HDPE	700–1000
Nylon, type 6	30–100
Nylon 6/6	15–300
Phenolic	0.4–0.8
Polyacetal	25
Polycarbonate	110
Polyester	300
Polypropylene	100–600
PTFE	250–350

Table 1.6 Tensile Strength of Selected Wrought Aluminum Alloys (*From [1]. Used with permission.*)

Alloy	Temper	TS (MPa)
1050	0	76
1050	H16	130
2024	0	185
2024	T361	495
3003	0	110
3003	H16	180
5050	0	145
5050	H34	195
6061	0	125
6061	T6, T651	310
7075	0	230
7075	T6, T651	570

Table 1.7 Density of Selected Materials, Mg/m³ (From [1]. Used with permission.)

Metal		Ceramic		Glass		Polymer	
Ag	10.50	Al ₂ O ₃	3.97–3.986	SiO ₂	2.20	ABS	1.05–1.07
Al	2.7	BN (cub)	3.49	SiO ₂ 10 wt% Na ₂ O	2.291	Acrylic	1.17–1.19
Au	19.28	BeO	3.01–3.03	SiO ₂ 19.55 wt% Na ₂ O	2.383	Epoxy	1.80–2.00
Co	8.8	MgO	3.581	SiO ₂ 29.20 wt% Na ₂ O	2.459	HDPE	0.96
Cr	7.19	SiC(hex)	3.217	SiO ₂ 39.66 wt% Na ₂ O	2.521	Nylon, type 6	1.12–1.14
Cu	8.93	Si ₃ N ₄ (α)	3.184	SiO ₂ 39.0 wt% CaO	2.746	Nylon 6/6	1.13–1.15
Fe	7.87	Si ₃ N ₄ (β)	3.187			Phenolic	1.32–1.46
Ni	8.91	TiO ₂ (rutile)	4.25			Polyacetal	1.425
Pb	11.34	UO ₂	10.949–10.97			Polycarbonate	1.2
Pt	21.44	ZrO ₂ (CaO)	5.5			Polyester	1.31
Ti	4.51	Al ₂ O ₃ MgO	3.580			Polystyrene	1.04
W	19.25	3Al ₂ O ₃ 2SiO ₂	2.6–3.26			PTFE	2.1–2.3

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Table 1.8 Dielectric Constants of Ceramics (*From [1]. Used with permission.*)

Material	Dielectric constant, 10 ⁶ Hz	Dielectric strength V/mil	Volume resistivity $\Omega \cdot \text{cm}$ (23°C)	Loss factor ^a
Alumina	4.5–8.4	40–160	10 ¹¹ –10 ¹⁴	0.0002–0.01
Corderite	4.5–5.4	40–250	10 ¹² –10 ¹⁴	0.004–0.012
Forsterite	6.2	240	10 ¹⁴	0.0004
Porcelain (dry process)	6.0–8.0	40–240	10 ¹² –10 ¹⁴	0.0003–0.02
Porcelain (wet process)	6.0–7.0	90–400	10 ¹² –10 ¹⁴	0.006–0.01
Porcelain, zircon	7.1–10.5	250–400	10 ¹³ –10 ¹⁵	0.0002–0.008
Steatite	5.5–7.5	200–400	10 ¹³ –10 ¹⁵	0.0002–0.004
Titanates (Ba, Sr, Ca, Mg, and Pb)	15–12.000	50–300	10 ⁸ –10 ¹⁵	0.0001–0.02
Titanium dioxide	14–110	100–210	10 ¹³ –10 ¹⁸	0.0002–0.005

^aPower factor \times dielectric constant equals loss factor.

Table 1.9 Dielectric Constants of Glass (*From [1]. Used with permission.*)

Type	Dielectric constant at 100 MHz (20°C)	Volume resistivity (350°C M $\Omega \cdot \text{cm}$)	Loss factor ^a
Corning 0010	6.32	10	0.015
Corning 0080	6.75	0.13	0.058
Corning 0120	6.65	100	0.012
Pyrex 1710	6.00	2,500	0.025
Pyrex 3320	4.71	–	0.019
Pyrex 7040	4.65	80	0.013
Pyrex 7050	4.77	16	0.017
Pyrex 7052	5.07	25	0.019
Pyrex 7060	4.70	13	0.018
Pyrex 7070	4.00	1,300	0.0048
Vycor 7230	3.83	–	0.0061
Pyrex 7720	4.50	16	0.014
Pyrex 7740	5.00	4	0.040
Pyrex 7750	4.28	50	0.011
Pyrex 7760	4.50	50	0.0081
Vycor 7900	3.9	130	0.0023
Vycor 7910	3.8	1,600	0.00091
Vycor 7911	3.8	4,000	0.00072
Corning 8870	9.5	5,000	0.0085
G.E. Clear (silica glass)	3.81	4,000–30,000	0.00038
Quartz (fused)	3.75–4.1 (1 MHz)	–	0.0002 1 MHz

^aPower factor \times dielectric constant equals loss factor.

Table 1.10 Dielectric Constants of Solids in the Temperature Range 17–22°C (From [1]. Used with permission.)

Material	Freq., Hz	Dielectric constant	Material	Freq., Hz	Dielectric Constant
Acetamide	4×10^8	4.0	Phenanthrene	4×10^8	2.80
Acetanilide	–	2.9	Phenol (10°C)	4×10^8	4.3
Acetic acid (2°C)	4×10^8	4.1	Phosphorus, red	10^8	4.1
Aluminum oleate	4×10^8	2.40	Phosphorus, yellow	10^8	3.6
Ammonium bromide	10^8	7.1	Potassium aluminum sulfate	10^6	3.8
Ammonium chloride	10^8	7.0	Potassium carbonate (15°C)	10^8	5.6
Antimony trichloride	10^8	5.34	Potassium chlorate	6×10^7	5.1
Apatite \perp optic axis	3×10^8	9.50	Potassium chloride	10^4	5.03
Apatite \parallel optic axis	3×10^8	7.41	Potassium chromate	6×10^7	7.3
Asphalt	$<3 \times 10^6$	2.68	Potassium iodide	6×10^7	5.6
Barium chloride (anhyd.)	6×10^7	11.4	Potassium nitrate	6×10^7	5.0
Barium chloride (2H ₂ O)	6×10^7	9.4	Potassium sulfate	6×10^7	5.9
Barium nitrate	6×10^7	5.9	Quartz \perp optic axis	3×10^7	4.34
Barium sulfate (15°C)	10^8	11.4	Quartz \parallel optic axis	3×10^7	4.27
Beryl \perp optic axis	10^4	7.02	Resorcinol	4×10^8	3.2
Beryl \parallel optic axis	10^4	6.08	Ruby \perp optic axis	10^4	13.27
Calcite \perp optic axis	10^4	8.5	Ruby \parallel optic axis	10^4	11.28
Calcite \parallel optic axis	10^4	8.0	Rutile \perp optic axis	10^8	86
Calcium carbonate	10^6	6.14	Rutile \parallel optic axis	10^8	170
Calcium fluoride	10^4	7.36	Selenium	10^8	6.6
Calcium sulfate (2H ₂ O)	10^4	5.66	Silver bromide	10^6	12.2
Cassiterite \perp optic axis	10^{12}	23.4	Silver chloride	10^6	11.2
Cassiterite \parallel optic axis	10^{12}	24	Silver cyanide	10^6	5.6
<i>d</i> -Cocaine	5×10^8	3.10	Smithsonite \perp optic axis	10^{12}	9.3
Cupric oleate	4×10^8	2.80	Smithsonite \parallel optic axis	10^{10}	9.4
Cupric oxide (15°C)	10^8	18.1	Sodium carbonate (anhyd.)	6×10^7	8.4
Cupric sulfate (anhyd.)	6×10^7	10.3	Sodium carbonate (10H ₂ O)	6×10^7	5.3
Cupric sulfate (5H ₂ O)	6×10^7	7.8	Sodium chloride	10^4	6.12
Diamond	10^8	5.5	Sodium nitrate	–	5.2
Diphenylmethane	4×10^8	2.7	Sodium oleate	4×10^8	2.75
Dolomite \perp optic axis	10^8	8.0	Sodium perchlorate	6×10^7	5.4
Dolomite \parallel optic axis	10^8	6.8	Sucrose (mean)	3×10^8	3.32
Ferrous oxide (15°C)	10^8	14.2	Sulfur (mean)	–	4.0
Iodine	10^8	4	Thallium chloride	10^6	46.9
Lead acetate	10^6	2.6	<i>p</i> -Toluidine	4×10^8	3.0
Lead carbonate (15°C)	10^8	18.6	Tourmaline \perp optic axis	10^4	7.10
Lead chloride	10^6	4.2	Tourmaline \parallel optic axis	10^4	6.3
Lead monoxide (15°C)	10^8	25.9	Urea	4×10^8	3.5
Lead nitrate	6×10^7	37.7	Zircon \perp, \parallel	10^8	12
Lead oleate	4×10^8	3.27			
Lead sulfate	10^6	14.3			
Lead sulfide (15°)	10^6	17.9			
Malachite (mean)	10^{12}	7.2			
Mercuric chloride	10^6	3.2			
Mercurous chloride	10^6	9.4			
Naphthalene	4×10^8	2.52			